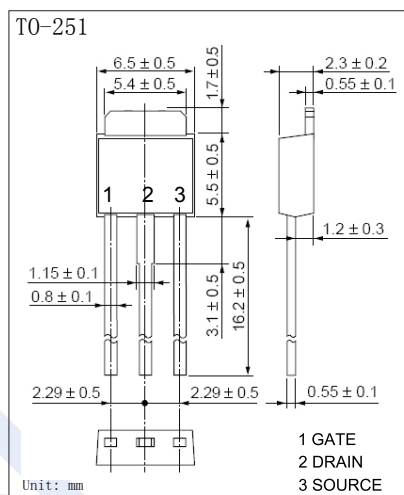
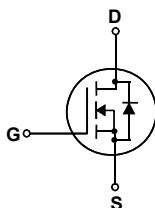


N-Channel Enhancement MOSFET

NDT6N65P

■ Features

- $V_{DS} (V) = 650V$
- $I_D = 4.8A$ ($V_{GS} = 10V$)
- $R_{DS(ON)} < 1.8\Omega$ ($V_{GS} = 10V$)
- Low gate charge (typical 16nC)



■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V_{DS}	650	V
Gate-Source Voltage		V_{GS}	± 30	
Continuous Drain Current	$T_c = 25^\circ C$	I_D	4.8	A
	$T_c = 100^\circ C$		3.0	
Pulsed Drain Current (Note.1)		I_{DM}	20	A
Avalanche Current (Note.1)		I_{AR}	4.8	
Repetitive Avalanche Energy (Note.1)		E_{AR}	9.5	mJ
Single Pulsed Avalanche Energy (Note.2)		E_{AS}	150	
Power Dissipation	$T_c = 25^\circ C$	P_D	95	W
	Derate above $25^\circ C$		0.76	W/ $^\circ C$
Peak Diode Recovery dv/dt (Note.3)		dv/dt	4.5	V/ns
Thermal Resistance.Junction- to-Ambient		R_{thJA}	110	$^\circ C/W$
Thermal Resistance.Junction- to-Case		R_{thJC}	1.3	
Thermal Resistance.Case-to-Sink Typ		R_{thJS}	50	
Maximum lead Temperature for soldering purpose, 1/8 from case for 5 seconds		T_L	300	$^\circ C$
Junction Temperature		T_J	150	
Storage Temperature Range		T_{stg}	-55 to 150	

Note.1: Repetitive Rating :Pulse width limited by maximum junction temperature

Note.2: $L=8mH, I_{AS}=6.0A, V_{DD}=50V, R_G=25\Omega$, Starting $T_J=25^\circ C$

Note.3: $I_{SD} \leq 4.8A, di/dt \leq 200A/us, V_{DD} \leq BV_{DSS}$, Starting $T_J=25^\circ C$

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■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	V _{DSS}	I _D =250 μA, V _{GS} =0V	650			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =650V, V _{GS} =0V			1	μA
		V _{DS} =520V, V _{GS} =0V, T _C =125℃			10	
Gate-Body Leakage Current	I _{GSS}	V _{DS} =0V, V _{GS} =±30V			±100	nA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250 μA	2.0		4.0	V
Static Drain-Source On-Resistance	R _{DS(on)}	V _{GS} =10V, I _D =2.4A		1.8	2.3	Ω
Input Capacitance	C _{iss}	V _{GS} =0V, V _{DS} =25V, f=1MHz		650		pF
Output Capacitance	C _{oss}			95		
Reverse Transfer Capacitance	C _{rss}			10		
Total Gate Charge	Q _g	V _{GS} =10V, V _{DS} =520V, I _D =6.0A (Note.1)		16		nC
Gate Source Charge	Q _{gs}			4.5		
Gate Drain Charge	Q _{gd}			5.0		
Turn-On DelayTime	t _{d(on)}	I _D =6.0A, V _{DS} =350V, R _{GEN} =25 Ω (Note.1)		30		ns
Turn-On Rise Time	t _r			40		
Turn-Off DelayTime	t _{d(off)}			80		
Turn-Off Fall Time	t _f			40		
Body Diode Reverse Recovery Time	t _{rr}	I _S = 6.0A, dI/dt= 100A/ μs V _{GS} =0V (Note.1)		280		μC
Body Diode Reverse Recovery Charge	Q _{rr}			2.0		
Maximum Body-Diode Continuous Current	I _S	Maximum Continuous Drain-Source Diode Forward Current			4.8	A
Maximum Pulsed Drain-Source Current	I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current			20	
Diode Forward Voltage	V _{SD}	I _S =4.8A, V _{GS} =0			1.4	V

Note.1: Pulse Test:Pulse width≤300us,Duty cycle≤2%

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■ Typical Characteristics

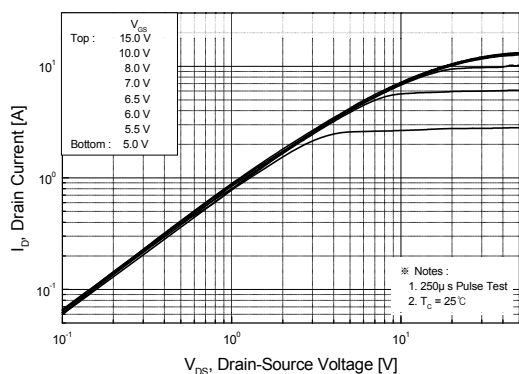


Figure 1. On-Region Characteristics

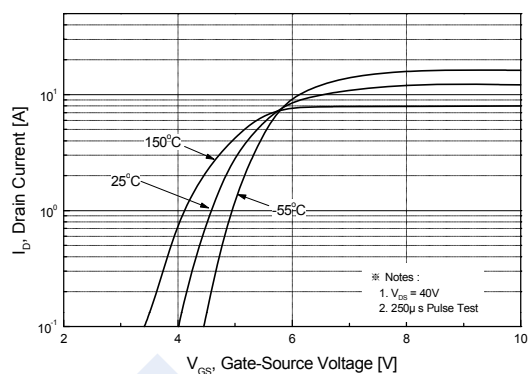


Figure 2. Transfer Characteristics

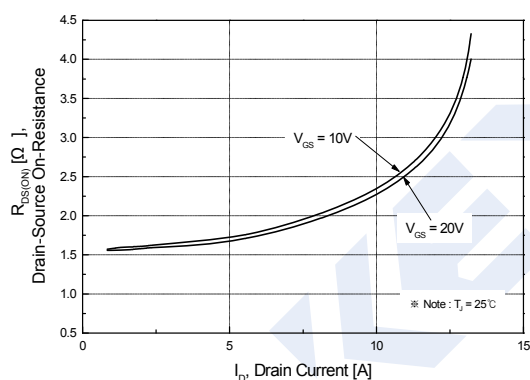


Figure 3. On-Resistance Variation vs Drain Current and Gate Voltage

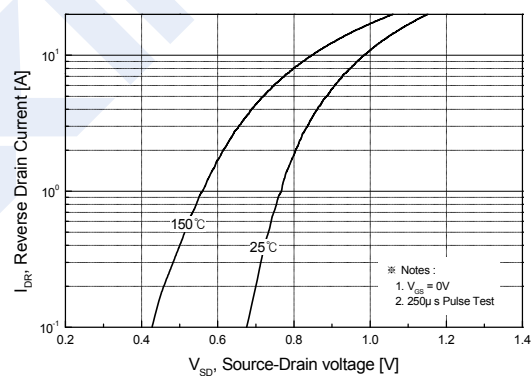


Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature

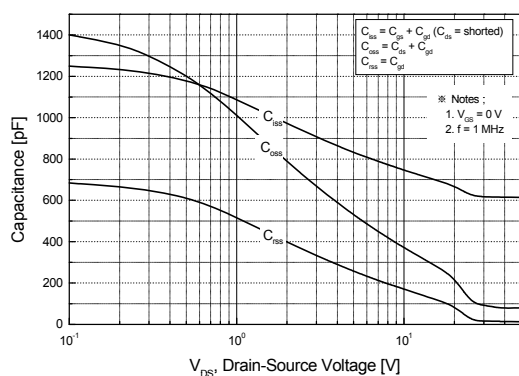


Figure 5. Capacitance Characteristics

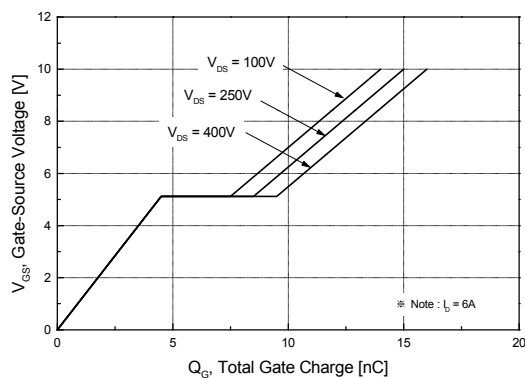


Figure 6. Gate Charge Characteristics

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■ Typical Characteristics

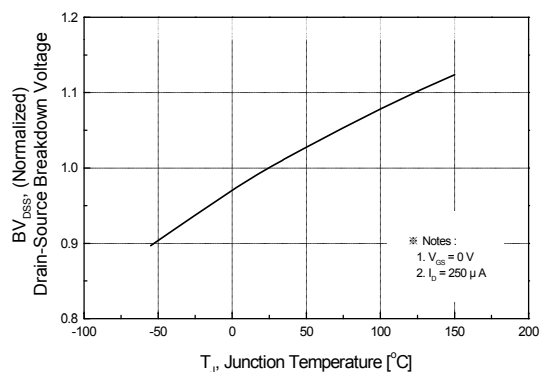


Figure 7. Breakdown Voltage Variation vs Temperature

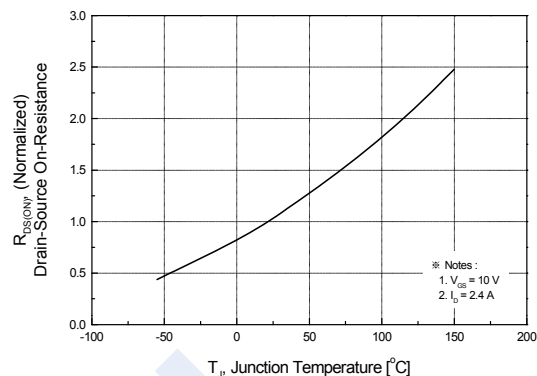


Figure 8. On-Resistance Variation vs Temperature

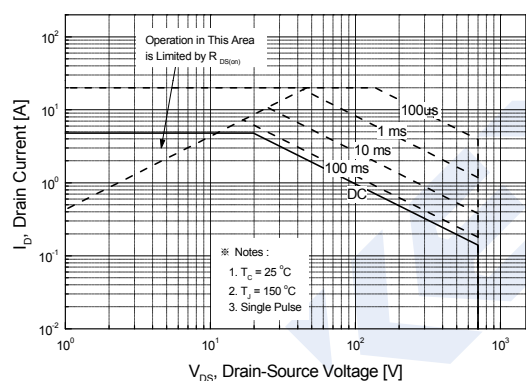


Figure 9. Maximum Safe Operating Area

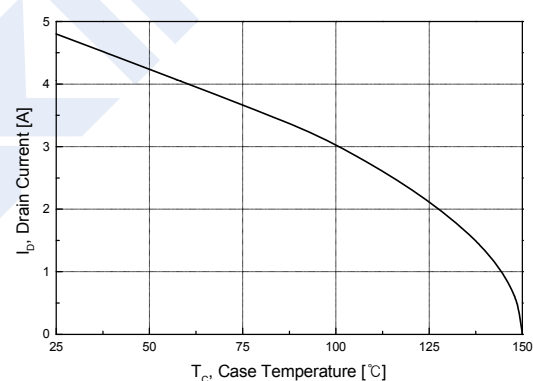


Figure 10. Maximum Drain Current vs Case Temperature

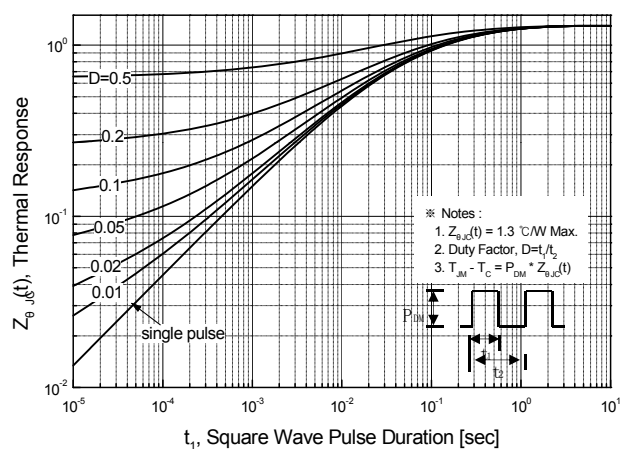


Figure 10. Maximum Drain Current vs Case Temperature